

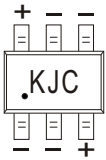
## Plastic-Encapsulate Diodes

SWITCHING DIODE

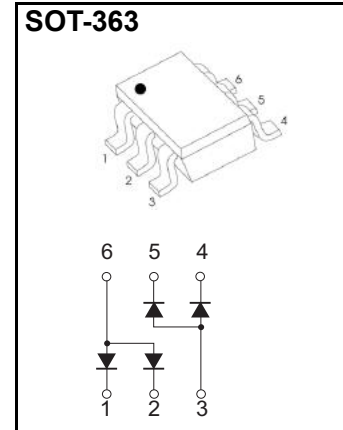
### FEATURES

- Fast Switching Speed
- Ultra-Small Surface Mount Package
- For General Purpose Switching Applications
- High Conductance

### MAKING: KJC



Solid dot = Pin1 indicate.  
Solid dot = Green molding compound device,  
if none, the normal device.



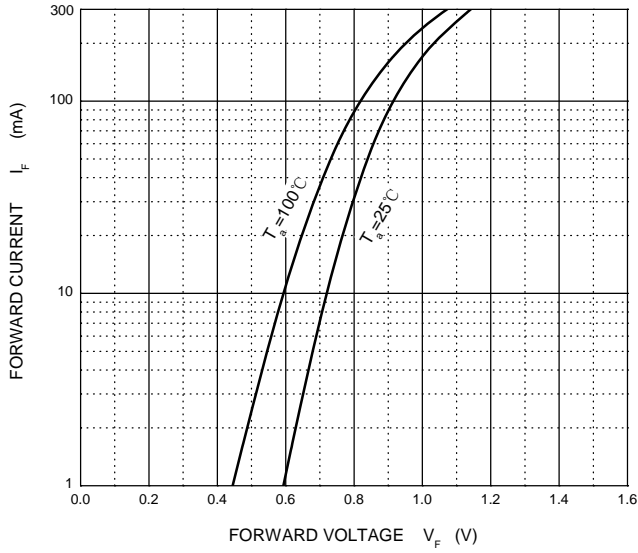
### Maximum Ratings @Ta=25°C

Parameter	Symbol	Limit	Unit
Peak Repetitive Peak Reverse Voltage	$V_{RRM}$	75	V
Working Peak Reverse Voltage	$V_{RWM}$		
DC Blocking Voltage	$V_R$		
Forward Continuous Current	$I_{FM}$	300	mA
Average Rectified Output Current	$I_O$	150	mA
Non-Repetitive Peak Forward Surge Current @ t=8.3ms	$I_{FSM}$	2	A
Power Dissipation	$P_D$	200	mW
Thermal Resistance From Junction to Ambient	$R_{\theta JA}$	625	°C/W
Operating Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{STG}$	-55~+150	°C

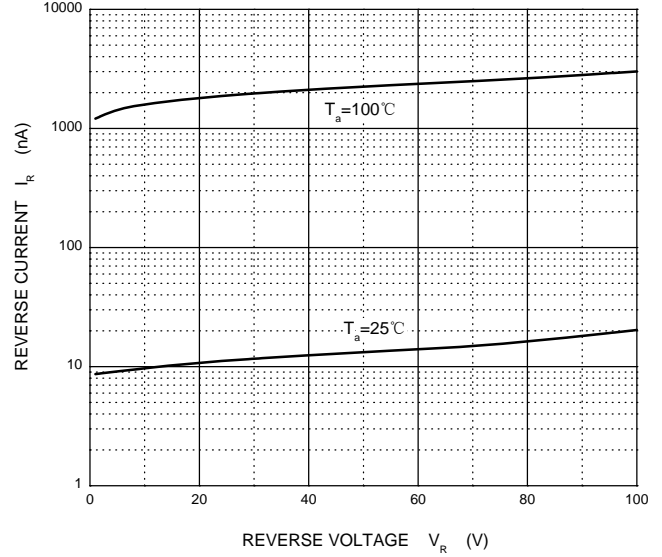
### ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 2.5\mu A$	75		V
Reverse voltage leakage current	$I_R$	$V_R = 75V$ $V_R = 20V$		2.5 0.025	$\mu A$
Forward voltage	$V_F$	$I_F = 1mA$ $I_F = 10mA$ $I_F = 50mA$ $I_F = 150mA$		715 855 1000 1250	mV
Capacitance between terminals	$C_T$	$V_R = 0, f = 1MHz$		2	pF
Reveres recovery time	$t_{rr}$	$I_F = I_R = 10mA, I_{rr} = 0.1 \times I_R,$ $R_L = 100\Omega$		4	ns

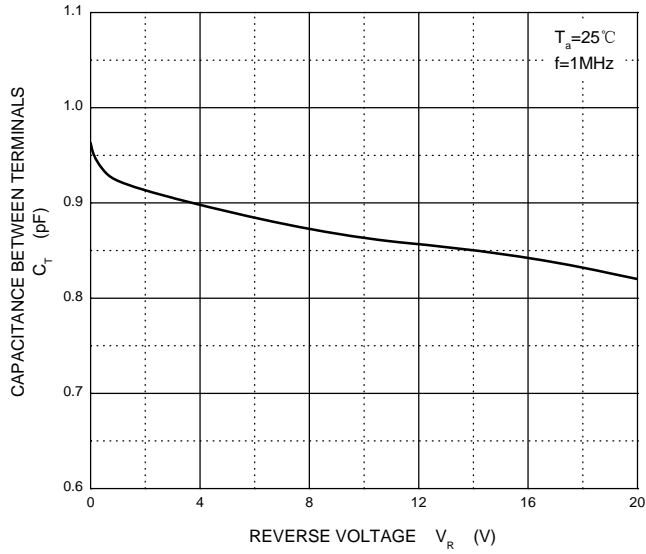
**Forward Characteristics**



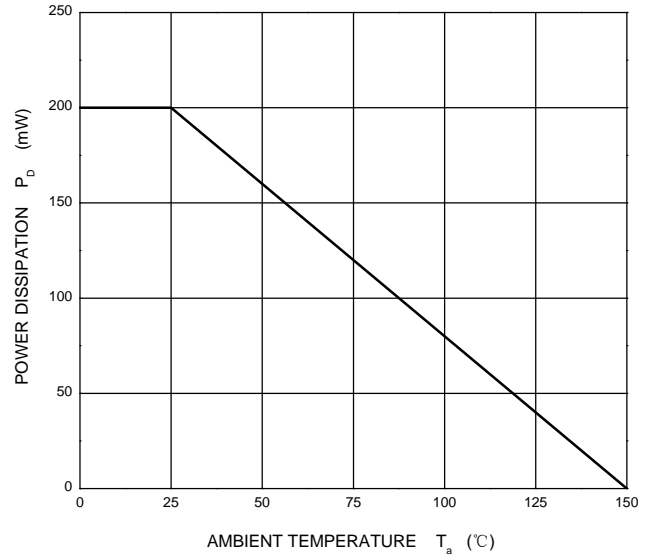
**Reverse Characteristics**



**Capacitance Characteristics**

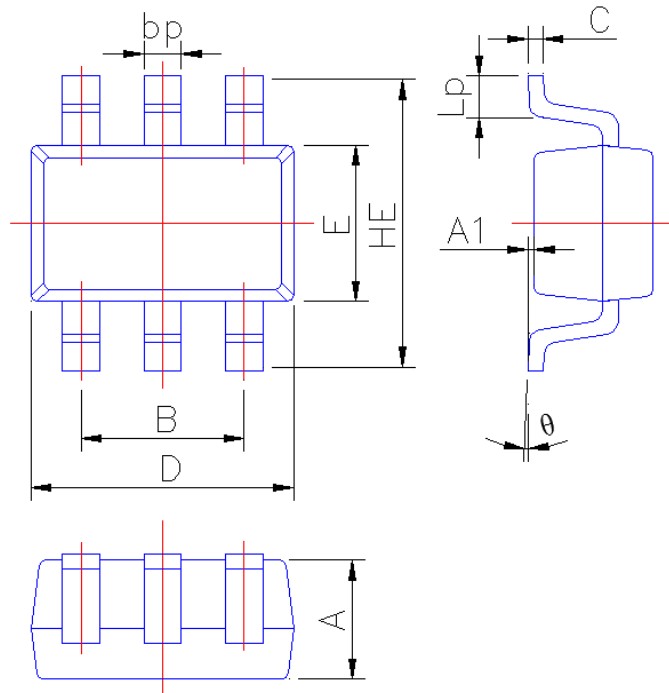


**Power Derating Curve**





## SOT-363-Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.00
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.45
C	0.09	0.15
D	2.00	2.20
E	1.15	1.35
HE	2.15	2.55
Lp	0.25	0.46
θ	0°	6°